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(71) Applicant (for all designated States except US): SHOWA DENKO K.K. [JP/JP]; 13-9, Shiba Daimon 1-chome, Minato-ku, Tokyo 105-8518 (JP).

(72) Inventors; and

(75) Inventors/Applicants (for US only): OHNO, Hiromoto [JP/JP]; C/O KAWASAKI PLANT, SHOWA DENKO K.K., 5-1, Ogimachi, Kawasaki-ku, Kawasaki-shi, Kanagawa 210-0867 (JP). OHI, Toshio [JP/JP]; C/O KAWASAKI PLANT, SHOWA DENKO K.K., 5-1, Ogimachi, Kawasaki-ku, Kawasaki-shi, Kanagawa 210-0867 (JP). YOSHIDA, Shuji [JP/JP]; c/o KAWASAKI PLANT, SHOWA DENKO K.K., 5-1, Ogimachi, Kawasaki-ku, Kawasaki-shi, KANAGAWA 210-0867 (JP). OHHIRA, Manabu [JP/JP]; c/o KAWASAKI PLANT, SHOWA DENKO K.K., 5-1, Ogimachi, Kawasaki-ku,

Kawasaki-shi, KANAGAWA 210-0867 (JP). TANAKA, Koutarou [JP/JP]; c/o SHOWA DENKO K.K., 5-1, Ogimachi, Kawasaki-ku, Kawasaki-shi, KANAGAWA 210-0867 (JP).

- (74) Agents: OHIE, Kunihisa et al.; Ohie Patent Office, Horiguchi No. 2 Building, 7F, 2-6, Hihonbashi-Ningyocho 2-chome, Chuo-ku, Tokyo 103-0013 (JP).
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(54) Title: CLEANING GAS FOR SEMICONDUCTOR PRODUCTION EQUIPMENT

(57) Abstract: The present invention relates to (1) a cleaning gas for cleaning semiconductor production equipment, obtained by mixing SF<sub>6</sub> and one or both of F<sub>2</sub> with and NF<sub>3</sub> with an inert gas at a specific ratio; (2) a cleaning gas for cleaning semiconductor production equipment, obtained by mixing SF6 and one or both of F2 and NF3 with an inert gas and an oxygen-containing gas at a specific ratio; (3) a method for cleaning semiconductor production equipment using the gas; and (4) a method for producing a semiconductor device including a cleaning step using the cleaning gas. By using the cleaning gas for semiconductor production equipment of the present invention which is high in the etching rate, efficient cleaning and production of semiconductor production equipment with excellent cost performance can be achieved.

